International Workshop
on Advanced Display
Materials

# FAPbBr<sub>3</sub> as a Potential Candidate for Resistive Random Access Memory (ReRAM)



Memoona Qammar and Jonathan E. Halpert\*‡

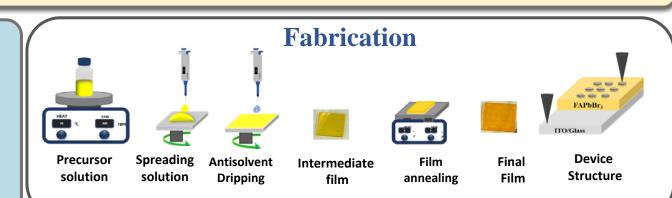
Department of Chemistry, Hong Kong University of Science and Technology (HKUST), Clear Water Bay Road, Kowloon, Hong Kong

#### Introduction

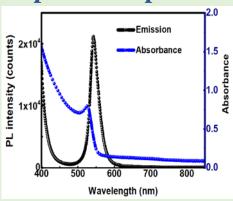
- Internet of things needs a new computing system with high-speed operation, low power consumption, and high scalability
- Organic halide perovskite memristors show strong hysteresis, simple structure, easy synthesis and unique optical and electronic properties
- The development for perovskites is hampered by material instability and susceptibility to moisture, oxygen and heat

### **Experimental**

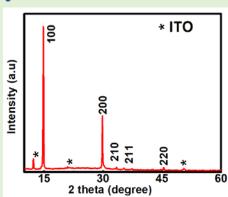
- Synthesis: Solution synthesis
- Fabrication: Spin-coating
- Electrode Deposition: Thermal evaporation
- Device structure: Metal—Insulator-Metal



## **Optical Properties Crystal structure Analysis**

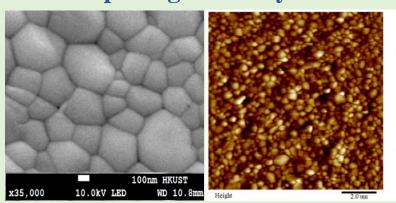


UV-VIS and PL spectra of FAPbBr<sub>3</sub>



X-ray diffraction analysis

#### Morphological analysis



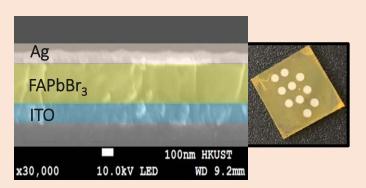
Scanning electron and atomic force microscopic image

**Device Characterization** 

50

#### **Device structure**

#### ITO/FAPbBr<sub>3</sub>/Ag

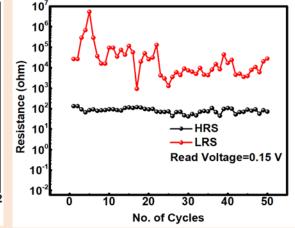


SEM cross-section and the real device

# 0.01 1E-3 1E-4 1E-5 1E-6 1E-7 1E-8 LRS LRS LRS HRS — 1 — 10 — 20 — 30 — 40

Semi log IV plot, switching between low current and high current state

Voltage (V)



HRS and LRS for 50 cycles

#### **Conclusion and Future Prospects**

Crystalline, uniform and smooth FAPBr<sub>3</sub> thin films having cubic structure and 2.27 eV band gap energy were formed successfully

1E-9

- As a result of DC sweep from  $-2.5 \text{ V} \rightarrow +2.0 \text{ V}$  the devices showed bipolar switching with electroforming voltage ranging from 0.8 to 1.1 V
- The endurance of devices is 50 cycles and on/off ratio is around 10<sup>2</sup>
- The HRS is fluctuating more as compared to LRS
- Bipolar switching, environmental and thermal stability and the IV results make this material potential candidate for future memristors

#### **■ References**

- Zhang Y. et al. ACS Energy Letters (2018): 1808-1814.
- Zeng F. et al. ACS Applied Materials & Interfaces (2020): 23094-23101.

#### ■ Acknowledgement

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